Shizuo Fujita

List of Publications by Year
in descending order

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142 papers	6,575 citations	76196 40 h-index	66788 78 g-index
142 all docs	142 docs citations	142 times ranked	3731 citing authors

#	Article	IF	Citations
1	Novel p-type oxides with corundum structure for gallium oxide electronics. Journal of Materials Research, 2022, 37, 651-659.	1.2	7
2	Prospects for phase engineering of semi-stable Ga2O3 semiconductor thin films using mist chemical vapor deposition. Journal of Applied Physics, 2022, 131, .	1.1	31
3	Analysis of Deep Traps in Mist Chemical Vapor Depositionâ€Grown nâ€Type Î±â€Ga₂O₃ by Photocapacitance Method. Physica Status Solidi (B): Basic Research, 2021, 258, 2000622.	0.7	6
4	Thermal stability of Î±-(Al_xGa_{1â€“x})₂O₃films grown on c-plane sapphire substrates with an Al composition up to 90%. Japanese Journal of Applied Physics, 2021, 60, SBBD13.	0.8	13
5	Ultra-wide bandgap corundum-structured p-type Î± -(Ir,Ga)2O3 alloys for Î± -Ga2O3 electronics. Applied Physics Letters, 2021, 118, .	1.5	36
6	Identification of free and bound exciton emission of MgO single crystal in vacuum ultraviolet spectral range. Applied Physics Letters, 2021, 119, .	1.5	7
7	Research of Semiconductor Materials That Emit in the Vacuum Ultraviolet Region of 200 nm or Less. Zairyo/Journal of the Society of Materials Science, Japan, 2021, 70, 727-731.	0.1	0
8	Thermal stability of Î±-Ga2O3 films grown on c-plane sapphire substrates via mist-CVD. AIP Advances, 2020, 10, .	0.6	26
9	Impact of hydrochloric acid on the epitaxial growth of In₂O₃ films on (0001)Î±-Al₂O₃ substrates by mist CVD. Applied Physics Express, 2020, 13, 075504.	1.1	6
10	Enhancement of epitaxial lateral overgrowth in the mist chemical vapor deposition ofÎ±-Ga₂O₃by using a-plane sapphire substrate. Japanese Journal of Applied Physics, 2019, 58, 120912.	0.8	28
11	Pure deep-ultraviolet cathodoluminescence from rocksalt-structured MgZnO grown with carbon-free precursors. Applied Physics Express, 2019, 12, 052011.	1.1	18
12	A power device material of corundum-structured Î±-Ga₂O₃fabricated by MIST EPITAXY^{Â®}technique. Japanese Journal of Applied Physics, 2018, 57, 02CB18.	0.8	76
13	Electrical characterization of Si-doped n-type Î±-Ga2O3 on sapphire substrates. MRS Advances, 2018, 3, 171-177.	0.5	41
14	Control of Crystal Structure of Ga₂O₃ on Sapphire Substrate by Introduction of Î±â€(Al_xGa_{1â^'x})₂O₃ Buffer Layer. Physica Status Solidi (B): Basic Research, 2018, 255, 1700326.	0.7	41
15	Evaluation of band alignment of Î±-Ga₂O₃/Î±-(Al_xGa_{1â^'}_x)₂O₃ by X-ray photoelectron spectroscopy. Japanese Journal of Applied Physics, 2018, 57, 040314.	1.5	43
16	Electrical properties of Î±-Ir2O3/Î±-Ga2O3 pn heterojunction diode and band alignment of the heterostructure. Applied Physics Letters, 2018, 113, .	1.5	74
17	Study on corundum-structured p-type iridium oxide thin films and band alignment at iridium oxide /gallium oxide hetero-junction. , 2018, , .		2
18	Tin oxide coating by nonvacuum-based mist chemical vapor deposition on stainless steel separators for polymer electrolyte fuel cells. Japanese Journal of Applied Physics, 2018, 57, 117103.	0.8	22

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19	Deep-Ultraviolet Luminescence of Rocksalt-Structured MgxZn1âˆ’xO (xâ€‰>â€‰0.5) Films on MgO Substrates. Journal of Electronic Materials, 2018, 47, 4356-4360.	1.0	15
20	Corundum-Structured Î±-In2O3 as a Wide-Bandgap Semiconductor for Electrical Devices. MRS Advances, 2017, 2, 301-307.	0.5	6
21	Corundum-strructured Î±-Ga<inf>2</inf>O<inf>3</inf>-based alloys for future power device applications. , 2017, , .		1
22	Crystal Growth and Device Applications of Corundum-Structured Gallium Oxide. Zairyo/Journal of the Society of Materials Science, Japan, 2016, 65, 631-637.	0.1	0
23	Silver oxide Schottky contacts and metal semiconductor field-effect transistors on SnO₂ thin films. Applied Physics Express, 2016, 9, 041101.	1.1	30
24	Characterization of band offset in Î±-(Al<inf>x</inf>Ga<inf>1-x</inf>)<inf>2</inf>O<inf>3</inf>/ Î±-Ga<inf>2</inf>O<inf>3</inf> heterostructures. , 2016, , .		1
25	Surface termination structure of Î±-Ga2O3 film grown by mist chemical vapor deposition. Applied Physics Letters, 2016, 108, 251602.	1.5	25
26	Evolution of oxide semiconductors for novel functional device applications. , 2016, , .		1
27	Evolution of corundum-structured III-oxide semiconductors: Growth, properties, and devices. Japanese Journal of Applied Physics, 2016, 55, 1202A3.	0.8	106
28	Homoepitaxial growth of beta gallium oxide films by mist chemical vapor deposition. Japanese Journal of Applied Physics, 2016, 55, 1202B8.	0.8	79
29	Fabrication of Î±-Ga<inf>2</inf>O<inf>3</inf> thin films using properties. , 2016, , .		0
30	Conductivity control of Sn-doped Î±-Ga₂O₃ thin films grown on sapphire substrates. Japanese Journal of Applied Physics, 2016, 55, 1202BA.	0.8	91
31	Growth of rocksalt-structured Mg_xZn_{1âˆ’} _xO (x > 0.5) films on MgO substrates and their deep-ultraviolet luminescence. Applied Physics Express, 2016, 9, 111102.	1.1	26
32	Reduction in edge dislocation density in corundum-structured Î±-Ga₂O₃ layers on sapphire substrates with quasi-graded Î±-(Al,Ga)₂O₃ buffer layers. Applied Physics Express, 2016, 9, 071101.	1.1	76
33	Growth characteristics of corundum-structured Î±-(Al Ga1âˆ’)2O3/Ga2O3 heterostructures on sapphire substrates. Journal of Crystal Growth, 2016, 436, 150-154.	0.7	72
34	Vertical Schottky barrier diodes of α-Ga<inf>2</inf>O<inf>3</inf> fabricated by mist epitaxy. , 2015, , .		6
35	Growth and metalâ€“oxideâ€“semiconductor field-effect transistors of corundum-structured alpha indium oxide semiconductors. Applied Physics Express, 2015, 8, 095503.	1.1	19
36	Enhanced thermal stability of alpha gallium oxide films supported by aluminum doping. Japanese Journal of Applied Physics, 2015, 54, 030301.	0.8	50

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37	Wide-bandgap semiconductor materials: For their full bloom. Japanese Journal of Applied Physics, 2015, 54, 030101.	0.8	266
38	Transparent conductive zinc-oxide-based films grown at low temperature by mist chemical vapor deposition. Thin Solid Films, 2015, 597, 30-38.	0.8	45
39	Aluminum Oxide Passivation Layer for Crystalline Silicon Solar Cells Deposited by Mist CVD in Open-Air Atmosphere. Materials Research Society Symposia Proceedings, 2014, 1647, 1.	0.1	0
40	Epitaxial growth of corundum-structured wide band gap III-oxide semiconductor thin films. Journal of Crystal Growth, 2014, 401, 588-592.	0.7	129
41	Mist deposition technology as a green route for thin film growth. , 2014, , .		1
42	Mist chemical vapor deposition of aluminum oxide thin films for rear surface passivation of crystalline silicon solar cells. Applied Physics Express, 2014, 7, 021303.	1.1	17
43	Ultrasonicâ€assisted mist chemical vapor deposition of IIâ€oxide and related oxide compounds. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1225-1228.	0.8	28
44	Growth of corundum-structured (In Ga1â˜)2O3 alloy thin films on sapphire substrates with buffer layers. Journal of Crystal Growth, 2014, 401, 670-672.	0.7	46
45	Band gap and function engineering for novel functional alloy semiconductors: Bloomed as magnetic properties at room temperature with Î±-(GaFe)2O3. Journal of Applied Physics, 2013, 113, .	1.1	62
46	Growth of corundum-structured In2O3 thin films on sapphire substrates with Fe2O3 buffer layers. Journal of Crystal Growth, 2013, 364, 30-33.	0.7	62
47	Formation of Semi-Insulating Layers on Semiconducting Î²-Ga‹sub›2‹/sub›O‹sub›3‹/sub› Single Crystals by Thermal Oxidation. Japanese Journal of Applied Physics, 2013, 52, 051101.	0.8	39
48	Thermal stability of single crystalline alpha gallium oxide films on sapphire substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1592-1595.	0.8	63
49	Fabrication of Corundum-Structured Î±-(InFe)2O3 Alloy Films on Sapphire Substrates by Inserting Î±-Fe2O3 Buffer Layer. Materials Research Society Symposia Proceedings, 2013, 1494, 221-225.	0.1	1
50	Crystal Structure of Non-Doped and Sn-Doped Î±-(GaFe)2O3 Thin Films.. Materials Research Society Symposia Proceedings, 2013, 1494, 147-152.	0.1	3
51	Oriented growth of beta gallium oxide thin films on yttriumâ€stabilized zirconia substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1596-1599.	0.8	23
52	Thin Film Formation of Transparent Conductive Oxides by Solution-Based Mist Deposition Method toward Hybrid Device Applications. Materials Research Society Symposia Proceedings, 2012, 1400, 1.	0.1	2
53	Fabrication of Organic Polymer Solar Cells by a Novel Solution-Based Vapor-like Mist Deposition Method. Materials Research Society Symposia Proceedings, 2012, 1390, 47.	0.1	3
54	Fabrication of Organic Small Molecular Thin Films based on Ultrasonic Spray-Assisted Vapor-Deposition Method. Materials Research Society Symposia Proceedings, 2012, 1400, 29.	0.1	0

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55	Growth and Band Gap Control of Corundum-Structured Î±-(AlGa)₂O₃ Thin Films on Sapphire by Spray-Assisted Mist Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2012, 51, 100207.	0.8	83
56	Formation of aluminum tris (8â€hydroxyquinoline) solution in methanol and fabrication of thin films by ultrasonic sprayâ€assisted vapor deposition. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1298-1301.	0.8	9
57	Evaluation of Misfit Relaxation in Î±-Ga₂O₃Epitaxial Growth on Î±-Al₂O₃Substrate. Japanese Journal of Applied Physics, 2012, 51, 020201.	0.8	20
58	Electrical Conductive Corundum-Structured Î±-Ga₂O₃Thin Films on Sapphire with Tin-Doping Grown by Spray-Assisted Mist Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2012, 51, 070203.	0.8	27
59	Fundamental Properties and Optical Device Applications of ZnO. The Review of Laser Engineering, 2011, 39, 165-170.	0.0	0
60	Extraction of Trap Densities in ZnO Thin-Film Transistors and Dependence on Oxygen Partial Pressure During Sputtering of ZnO Films. IEEE Transactions on Electron Devices, 2011, 58, 3018-3024.	1.6	24
61	Fabrication of PEDOT:PSS/ZnMgO Schottkyâ€type ultraviolet sensors on glass substrates with solutionâ€based mist deposition technique and hardâ€mask patterning. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 613-615.	0.8	23
62	Growth of SnO₂ crystalline thin films by mist chemical vapour deposition method. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 540-542.	0.8	46
63	Reduction of Photo-Leakage Current in ZnO Thin-Film Transistors With Dual-Gate Structure. IEEE Electron Device Letters, 2011, 32, 509-511.	2.2	9
64	Effects of chemical stoichiometry of channel region on bias instability in ZnO thin-film transistors. Applied Physics Letters, 2011, 98, .	1.5	17
65	Ultrasonic Spray-Assisted Solution-Based Vapor-Deposition of Aluminum Tris(8-hydroxyquinoline) Thin Films. Japanese Journal of Applied Physics, 2011, 50, 020204.	0.8	7
66	69.1: Photoâ€Leakage Current in ZnO TFTs for Transparent Electronics. Digest of Technical Papers SID International Symposium, 2010, 41, 1029-1032.	0.1	4
67	Growth characteristics of singleâ€crystalline ZnMgO layers by ultrasonic spray assisted mist CVD technique. Physica Status Solidi (B): Basic Research, 2010, 247, 1460-1463.	0.7	37
68	Corundumâ€structured Î±â€phase Ga₂O₃â€Cr₂O₃â€Fe₂O₃ alloy system for novel functions. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2467-2470.	0.8	35
69	Artificial Surface Control of Gallium Oxide Semiconductors and Growth of High Quality Single-crystalline Thin Films. Hyomen Kagaku, 2010, 31, 643-650.	0.0	0
70	Mechanism analysis of photoleakage current in ZnO thin-film transistors using device simulation. Applied Physics Letters, 2010, 97, 163503.	1.5	15
71	Analysis of Hump Characteristics in Thin-Film Transistors With ZnO Channels Deposited by Sputtering at Various Oxygen Partial Pressures. IEEE Electron Device Letters, 2010, , .	2.2	36
72	Flame Detection by a Î²-Ga₂O₃-Based Sensor. Japanese Journal of Applied Physics, 2009, 48, 011605.	0.8	142

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73	Î²-Al_{2x}Ga_{2-2x}O₃ Thin Film Growth by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2009, 48, 070202.	0.8	110
74	Epitaxial ZnO Thin Films ona-Plane Sapphire Substrates Grown by Ultrasonic Spray-Assisted Mist Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2009, 48, 121103.	0.8	45
75	Mist Deposition Technique as a Green Chemical Route for Synthesizing Oxide and Organic Thin Films. Materials Research Society Symposia Proceedings, 2009, 1220, 4061.	0.1	3
76	Properties of Ga₂O₃â€based (In_x) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 627 Td (Ga<sub> epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3113-3115.	0.8	75
77	An approach for single crystalline zinc oxide thin films with fine channel mist chemical vapor deposition method. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3138-3140.	0.8	30
78	Step-flow growth of homoepitaxial ZnO thin films by ultrasonic spray-assisted MOVPE. Journal of Crystal Growth, 2008, 310, 5007-5010.	0.7	23
79	Surface morphology of homoepitaxial Î²-Ga2O3 thin films grown by molecular beam epitaxy. Thin Solid Films, 2008, 516, 5768-5771.	0.8	128
80	Heteroepitaxy of Corundum-Structured Î±-Ga₂O₃ Thin Films on Î±-Al₂O₃ Substrates by Ultrasonic Mist Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2008, 47, 7311.	0.8	405
81	Growth of Crystalline Zinc Oxide Thin Films by Fine-Channel-Mist Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2008, 47, 4669.	0.8	109
82	Vertical Solar-Blind Deep-Ultraviolet Schottky Photodetectors Based on Î²-Ga₂O₃Substrates. Applied Physics Express, 2008, 1, 011202.	1.1	342
83	Ultrasonic spray assisted Mist-CVD method for high-quality crystalline and amorphous oxide semiconductors growth. Materials Research Society Symposia Proceedings, 2008, 1113, 1.	0.1	0
84	Ga₂O₃ Thin Film Growth on c-Plane Sapphire Substrates by Molecular Beam Epitaxy for Deep-Ultraviolet Photodetectors. Japanese Journal of Applied Physics, 2007, 46, 7217.	0.8	480
85	Low-Temperature Growth of ZnO Thin Films by Linear Source Ultrasonic Spray Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2007, 46, 6811-6813.	0.8	65
86	Direct Fabrication of ZnO Whiskers Bridging Between Micron-gap Electrodes in Aqueous Solution for Highly Gas Sensing. Materials Research Society Symposia Proceedings, 2007, 1035, 1.	0.1	0
87	Linear-Source Ultrasonic Spray Chemical Vapor Deposition Method for Fabrication of ZnMgO Films and Ultraviolet Photodetectors. Japanese Journal of Applied Physics, 2006, 45, L857-L859.	0.8	87
88	Fabrication and Properties of ZnO Thin Films Prepared by Fine Channel Mist Mehtod. Zairyo/Journal of the Society of Materials Science, Japan, 2006, 55, 153-158.	0.1	32
89	High electron concentration and mobility in Al-doped n-ZnO epilayer achieved via dopant activation using rapid-thermal annealing. Journal of Applied Physics, 2005, 97, 066103.	1.1	106
90	Fabrication of wide-band-gap MgxZn1âˆ’xO quasi-ternary alloys by molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 192911.	1.5	88

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91	Molecular Beam Epitaxy of High Magnesium Content Single-Phase Wurzite MgxZn1-xO Alloys ($xsimeq) Tj ETQq1 1 0.784314 rgBT /Ov 2003, 42, L401-L403.	0.8	156
92	Selective formation of ZnO nanodots on nanopatterned substrates by metalorganic chemical vapor deposition. Applied Physics Letters, 2003, 83, 3593-3595.	1.5	42
93	Self-organized ZnO quantum dots on SiO2/Si substrates by metalorganic chemical vapor deposition. Applied Physics Letters, 2002, 81, 5036-5038.	1.5	140
94	Hexagonal GaN grown on GaAs{11n} substrates by metalorganic vapor-phase epitaxy using AlAs intermediate layers. Applied Physics Letters, 2001, 79, 4133-4135.	1.5	7
95	Vacuum Deposition and Luminescence Dynamics of Organic Thin Film Multi-Structures. Shinku/Journal of the Vacuum Society of Japan, 2001, 44, 948-955.	0.2	0
96	Single-phase hexagonal GaN grown on AlAs/GaAs(001). Applied Physics Letters, 2000, 77, 244-246.	1.5	7
97	Six-bilayer periodic structures in GaN grown on GaAs(001). Applied Physics Letters, 2000, 76, 330-332.	1.5	5
98	Integration of GaN with Si using a AuGe-mediated wafer bonding technique. Applied Physics Letters, 2000, 77, 3959-3961.	1.5	16
99	Electrical Characterization of MOVPE-Grown P-Type GaN:Mg Against Annealing Temperature. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 665-670.	1.0	2
100	Tunable band offsets via control of interface atomic configuration in GaAs-on-ZnSe(001) heterovalent heterostructures. Journal of Applied Physics, 1999, 85, 1514-1519.	1.1	5
101	Relation between GaAs surface morphology and incorporation of hexagonal GaN into cubic GaN. Journal of Crystal Growth, 1999, 196, 41-46.	0.7	19
102	Luminescence Dynamics of Alq3-Based Multilayer Structures in Terms of HOMO and LUMO Energy Discontinuity. Materials Research Society Symposia Proceedings, 1999, 598, 321.	0.1	0
103	Growth of p-type Zn(S)Se layers by MOVPE. Journal of Crystal Growth, 1998, 184-185, 398-405.	0.7	11
104	A comparative study on deep levels in p-ZnSe grown by MBE, MOMBE and MOVPE. Journal of Crystal Growth, 1998, 184-185, 495-499.	0.7	3
105	The mechanism of radiative recombination in light-emitting devices composed on InGaN quantum wells. Electronics and Communications in Japan, 1998, 81, 45-56.	0.2	3
106	Nucleation processes during metalorganic vapor phase epitaxy of ZnSe on GaAs(001). Journal of Applied Physics, 1998, 84, 1383-1388.	1.1	2
107	Deep states in nitrogen-doped p-ZnSe. Journal of Applied Physics, 1998, 83, 2563-2567.	1.1	5
108	Optical Absorption in ZnSe-GaAs Heterovalent Quantum Structures. Materials Research Society Symposia Proceedings, 1998, 535, 71.	0.1	0

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109	Electrical Characterization of MOVPE-GROWN P-Type GaN:Mg Against Annealing Temperature. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	2
110	Stimulated emission from optically pumped GaN quantum dots. Applied Physics Letters, 1997, 71, 1299-1301.	1.5	84
111	Tunable band offsets in ZnSe/GaAs heterovalent heterostructures grown by metalorganic vapor phase epitaxy. Journal of Applied Physics, 1997, 82, 2984-2989.	1.1	14
112	Self-organized CdSe quantum dots onto cleaved GaAs (110) originating from Stranskiâ€"Krastanow growth mode. Applied Physics Letters, 1997, 70, 3278-3280.	1.5	61
113	Role of self-formed InGaN quantum dots for exciton localization in the purple laser diode emitting at 420 nm. Applied Physics Letters, 1997, 70, 981-983.	1.5	907
114	Title is missing!. Journal of Materials Science Letters, 1997, 16, 1187-1190.	0.5	0
115	Effect of cleaving environment on the growth of ZnSe on the GaAs (110) surface by molecular beam epitaxy. Journal of Materials Science Letters, 1997, 16, 1187-1190.	0.5	0
116	Molecular Beam Epitaxial Growth Behaviors of Zn1-xCdxSe on the GaAs(110) Surface Cleaved in Ultra High Vacuum.. Shinku/Journal of the Vacuum Society of Japan, 1997, 40, 317-320.	0.2	0
117	Defect States In p-ZnSe:N Grown By MOVPE. Materials Research Society Symposia Proceedings, 1996, 442, 561.	0.1	0
118	Surface Reconstruction and Morphology of Hydrogen Sulfide Treated GaAs (001) Substrate. Materials Research Society Symposia Proceedings, 1996, 448, 15.	0.1	0
119	Emission Mechanism of the InGaN MQW Grown by MOCVD. Materials Research Society Symposia Proceedings, 1996, 449, 665.	0.1	0
120	Effects of GaAs buffer layer and lattice-matching on deep levels in Zn(S)Se/GaAs heterostructures. Journal of Electronic Materials, 1996, 25, 217-222.	1.0	7
121	Growth of P-type Znse by metalorganic molecular beam epitaxy using metal Zn and dimethylselenide. Journal of Electronic Materials, 1996, 25, 223-227.	1.0	4
122	Effects of annealing atmosphere and temperature on acceptor activation in ZnSe:N grown by photoassisted MOVPE. Journal of Crystal Growth, 1996, 159, 312-316.	0.7	49
123	MO(GS)MBE and photo-MO(GS)MBE of IIâ€"VI semiconductors. Journal of Crystal Growth, 1996, 164, 196-201.	0.7	11
124	Photoassisted growth of IIâ€"VI semiconductor films. Applied Surface Science, 1995, 86, 431-436.	3.1	11
125	Growth of ZnSe/ZnMgSSe quantum well structures by metalorganic molecular beam epitaxy under in situ observation of reflection high energy electron diffraction intensity oscillation. Journal of Crystal Growth, 1995, 150, 738-742.	0.7	3
126	Thermal annealing effects on p-type conductivity of nitrogendoped ZnSe grown by metalorganic vapor phase epitaxy. Journal of Electronic Materials, 1995, 24, 137-141.	1.0	17

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127	Gas-Source Molecular Beam Epitaxial Growth of (Zn, Mg)(S, Se) Using Bis-methylcyclopentadienyl-magnesium and Hydrogen Sulfide. Japanese Journal of Applied Physics, 1994, 33, L290-L293.	0.8	16
128	Photocatalytic surface reactions in metalorganic vapor-phase epitaxy. Applied Surface Science, 1994, 79-80, 41-46.	3.1	7
129	Photo-assisted metalorganic vapor-phase epitaxy for nitrogen doping and fabrication of blue-green light emitting devices of ZnSe-based semiconductors. Journal of Crystal Growth, 1994, 138, 737-744.	0.7	15
130	Metalorganic vapor-phase epitaxy of p-type ZnSe and p/n junction diodes. Journal of Crystal Growth, 1994, 145, 552-556.	0.7	19
131	Metalorganic vapor phase epitaxy growth and nitrogen-doping of ZnxCd1-xS using photo-assistance. Journal of Crystal Growth, 1994, 145, 570-575.	0.7	5
132	Fabrication of IIâ€“VI semiconductor quantum well structures in ZnCdSSe alloy systems. Physica B: Condensed Matter, 1993, 191, 57-70.	1.3	10
133	Photoassisted Metalorganic Vapor-Phase Epitaxy of Nitrogen-Doped ZnSe Using Tertiarybutylamine as Doping Source. Japanese Journal of Applied Physics, 1993, 32, L1153-L1156.	0.8	21
134	Optically Pumped Blue-Green Laser Operation Above Room-Temperature in Zn0.80Cd0.20Se-ZnS0.08Se0.92Multiple Quantum Well Structures Grown by Metalorganic Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1991, 30, L605-L607.	0.8	47
135	A Defect Model for Photoirradiated Semiconductors â€“Suppression of the Self-Compensation in II-VI Materialsâ€“. Japanese Journal of Applied Physics, 1991, 30, 3475-3481.	0.8	32
136	Organometallic vapor-phase epitaxial growth of cubic ZnCdS lattice-matched to GaAs substrate. Journal of Crystal Growth, 1990, 99, 437-440.	0.7	24
137	Metalorganic Molecular Beam Epitaxial Growth of ZnSe and ZnS on GaAs Substrates Pretreated with (NH4)2SxSolution. Japanese Journal of Applied Physics, 1990, 29, L144-L147.	0.8	52
138	Rheed and x-ray characterization of InGaAs/GaAs grown by MBE. Journal of Crystal Growth, 1989, 95, 224-227.	0.7	39
139	Growth Rate Enhancement by Xenon Lamp Irradiation in Organometallic Vapor-Phase Epitaxy of ZnSe. Japanese Journal of Applied Physics, 1987, 26, L2000-L2002.	0.8	72
140	Fabrication of Highly Crystalline Corundum-Structured Î±-(Ga_{1-x}Fe_x)₂O₃Alloy Thin Films on Sapphire Substrates. Applied Physics Express, 0, 2, 075501.	1.1	83
141	Mist Chemical Vapor Deposition Growth of Î±â€In 2 O 3 Films Using Indium Oxide Powder as Source Precursor. Physica Status Solidi (B): Basic Research, 0, , 2100414.	0.7	3
142	VUV emission properties of rocksaltâ€structured MgZnO microcrystals prepared on quartz glass substrates. Physica Status Solidi (B): Basic Research, 0, , 2100354.	0.7	1